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(54) **DISPLAY DEVICE**

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**1/133707** (2013.01); **G02F 2001/134345**  
(2013.01)

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See application file for complete search history.

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(57) **ABSTRACT**

A display device capable of reducing a resistance of a common electrode is presented. The display device includes: a substrate; a gate line, a data line, and a storage electrode line formed on the substrate; a thin film transistor connected to the gate line and the data line; a pixel electrode connected with the thin film transistor; a common electrode formed on the pixel electrode; a plurality of microcavities between the common electrode and the pixel electrode; a roof layer formed on the common electrode; a liquid crystal layer in the microcavity; and an encapsulation layer formed on the roof layer to seal the microcavity, wherein the common electrode is connected with the storage electrode line at a position adjacent to the data line.

**13 Claims, 9 Drawing Sheets**

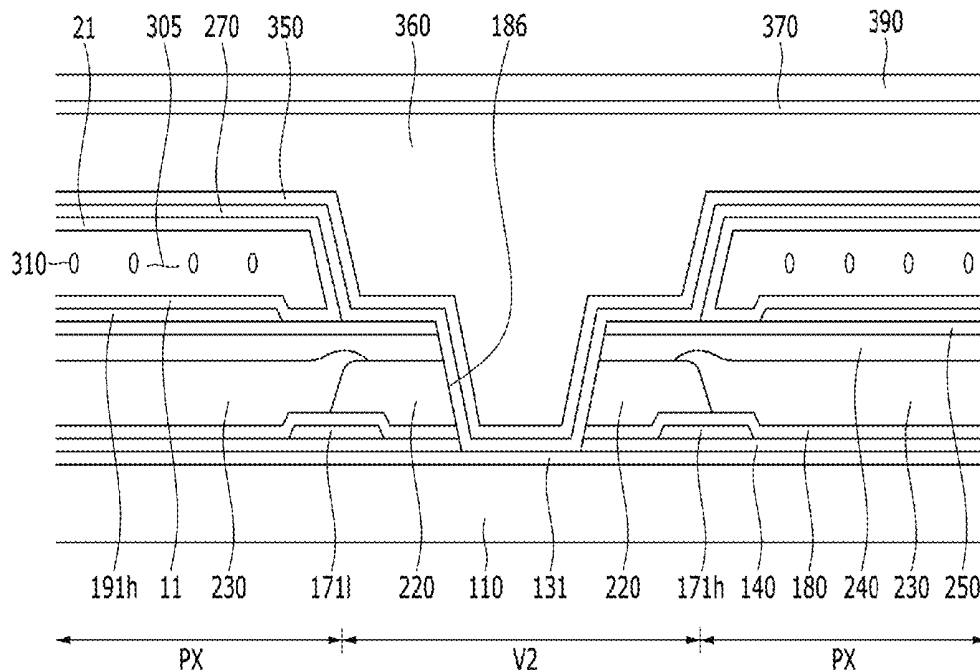


FIG. 1

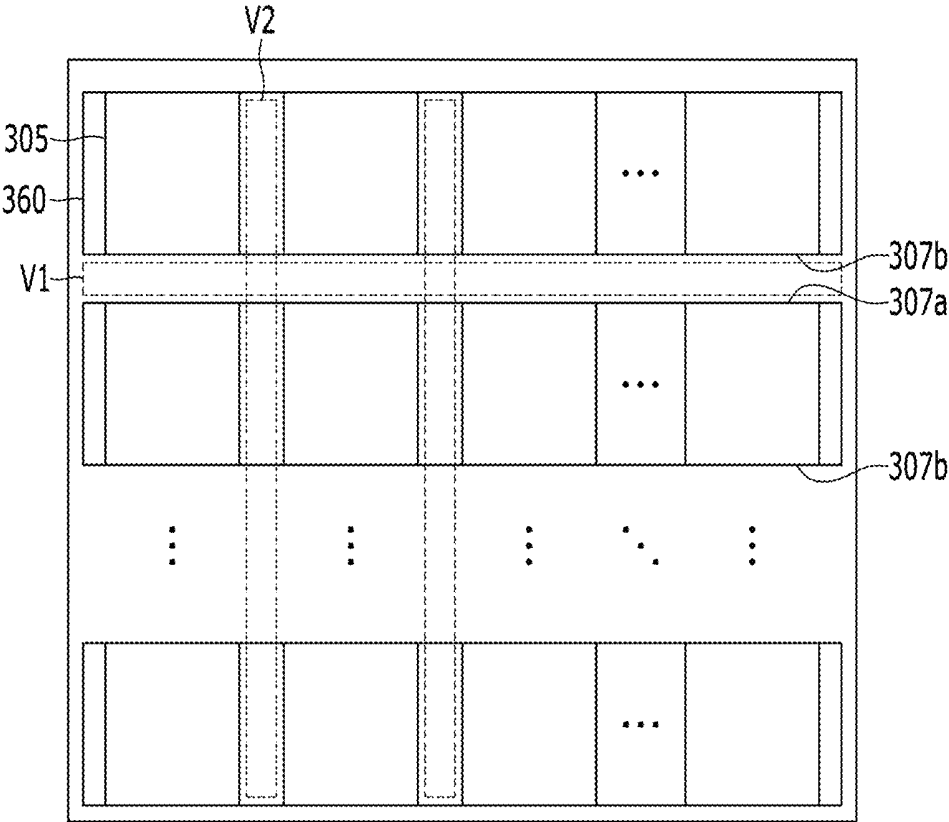


FIG. 2

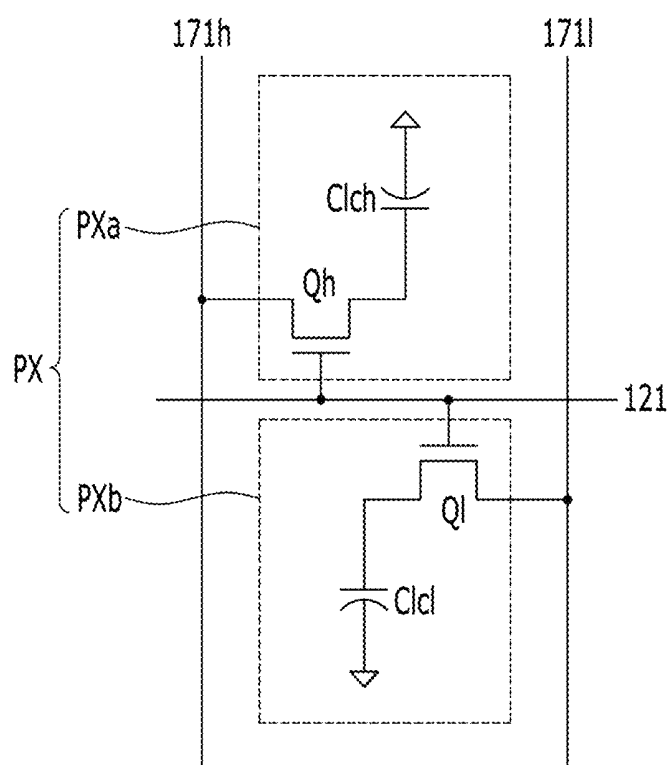


FIG. 3

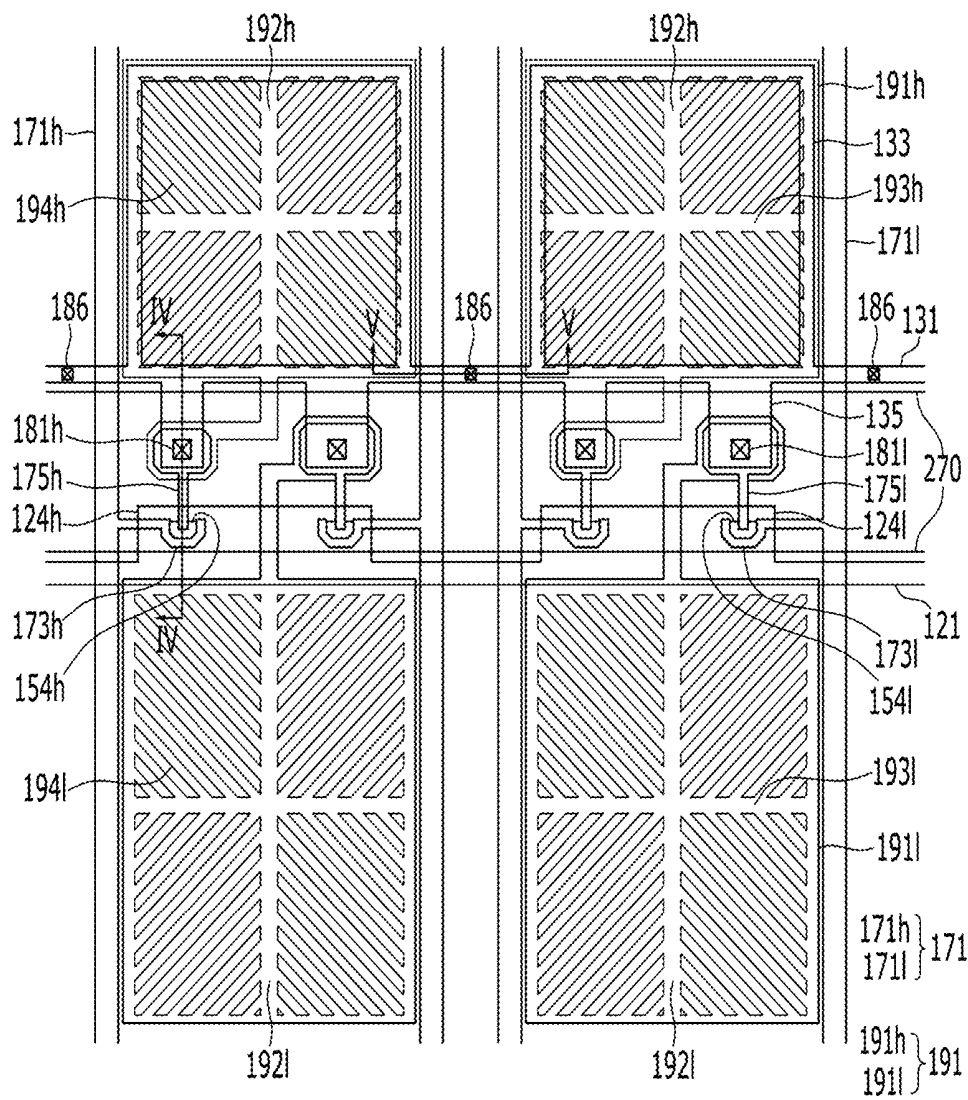


FIG. 4

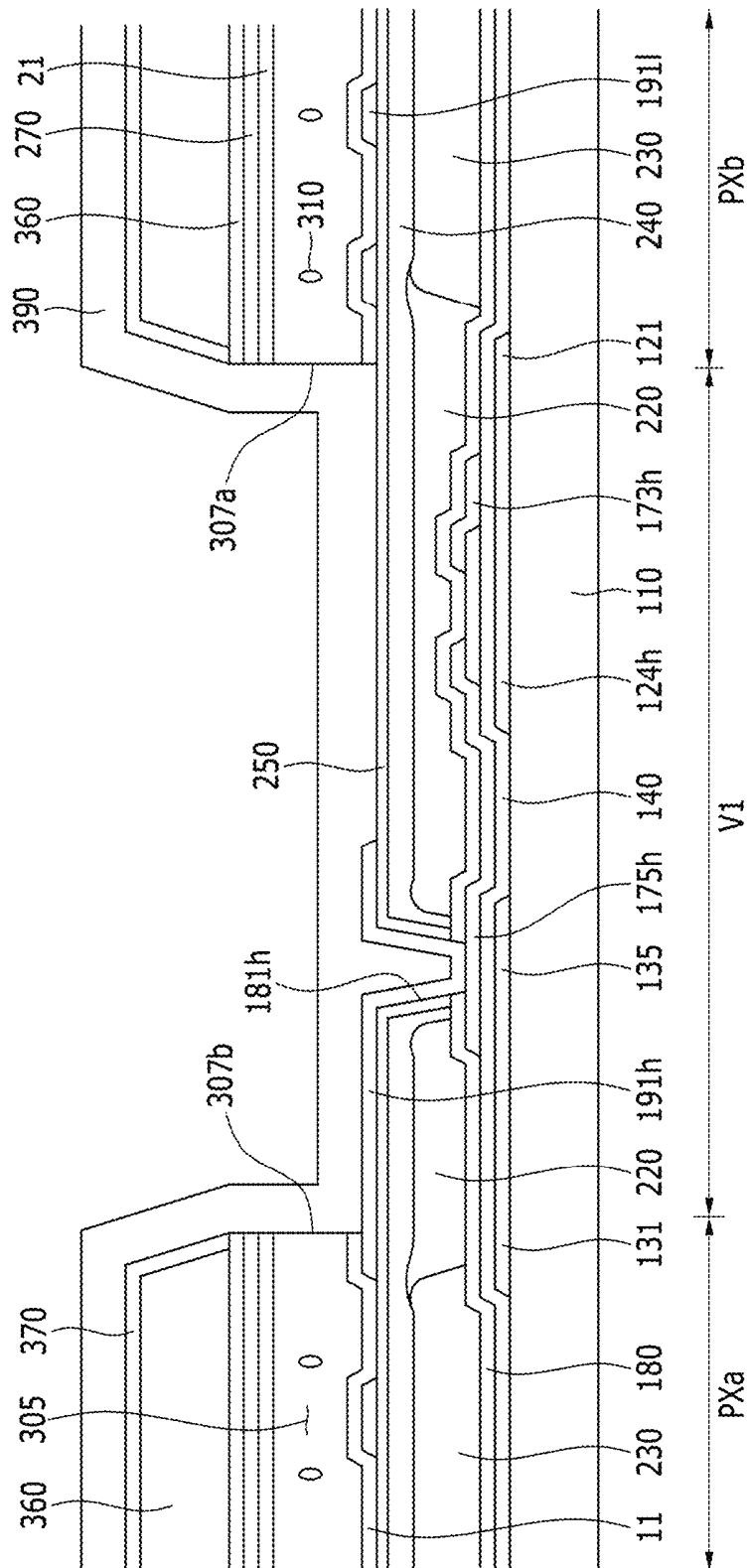


FIG. 5

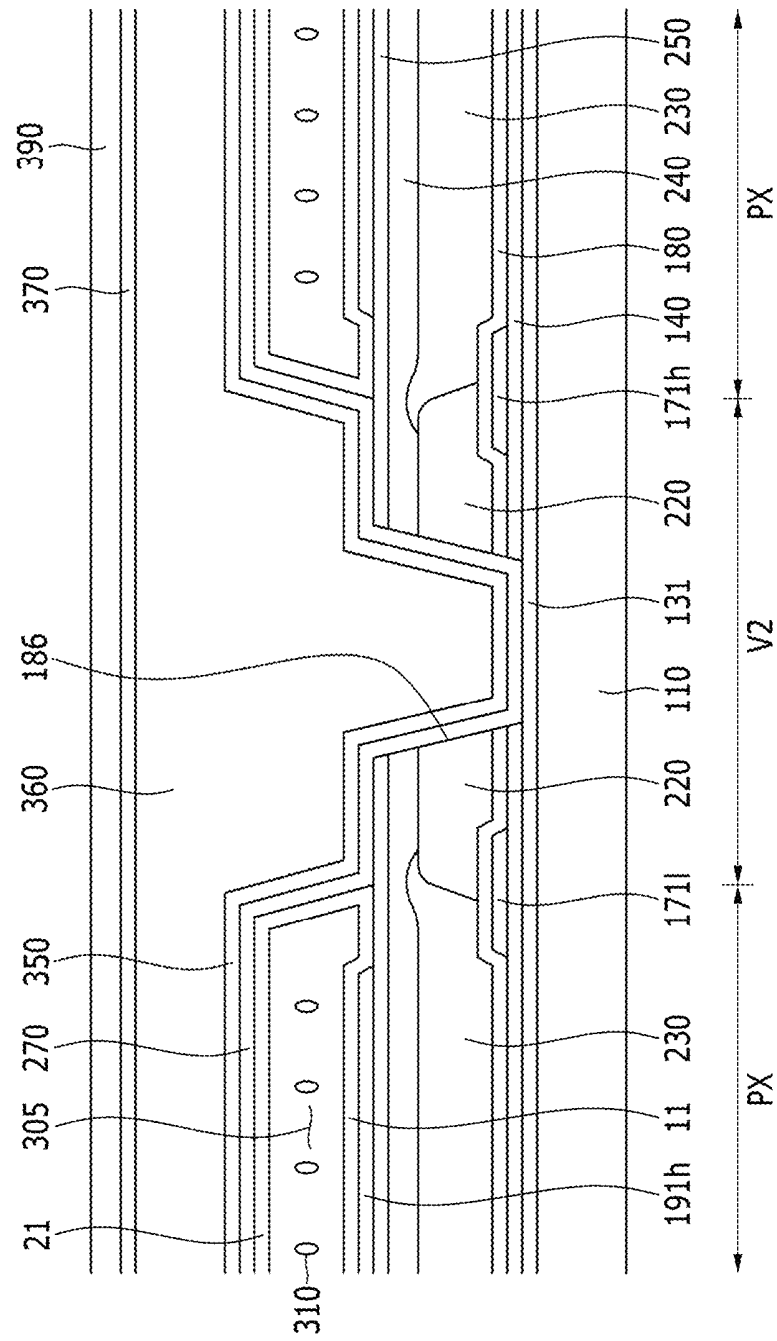


FIG. 6

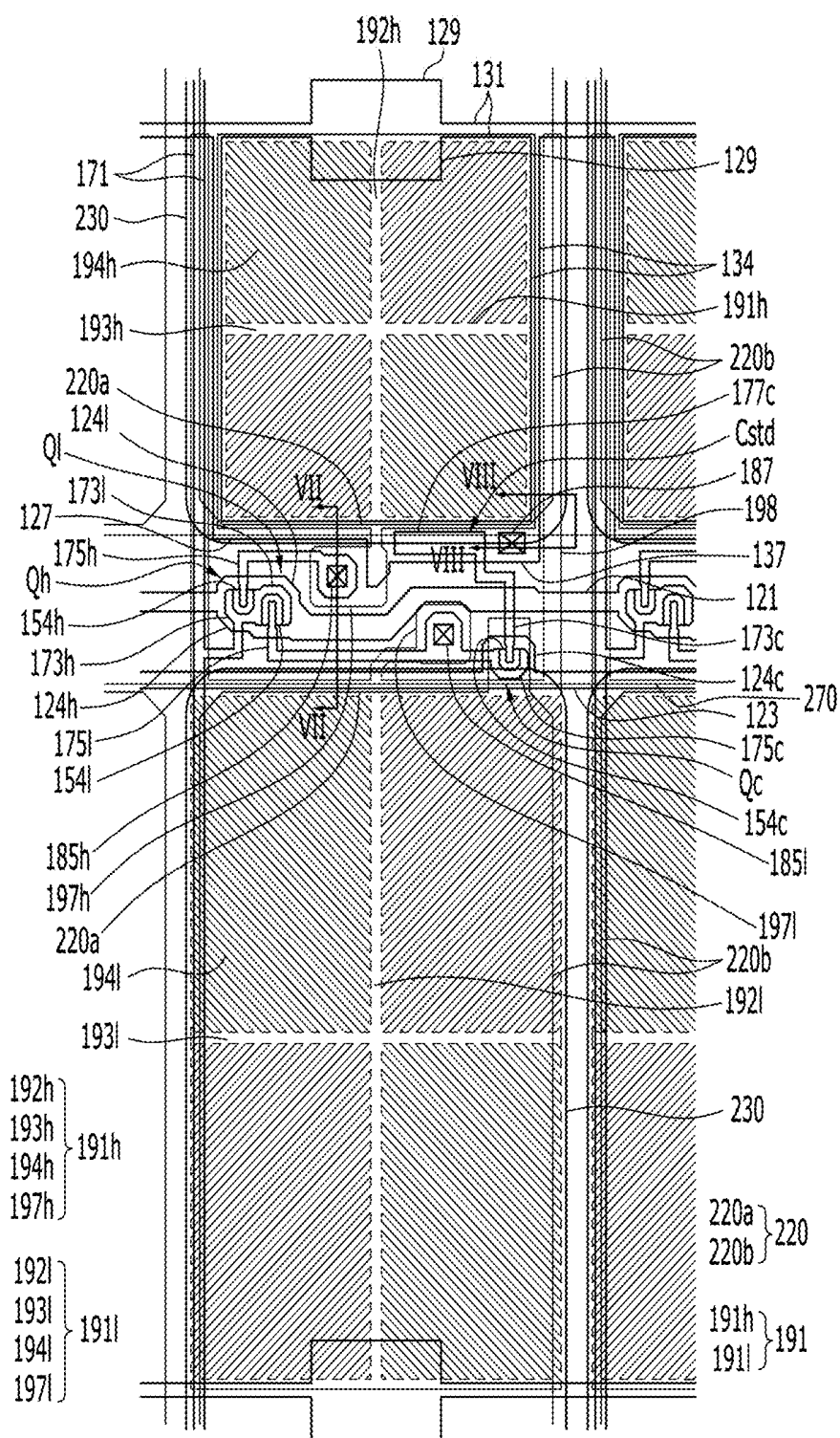


FIG. 7

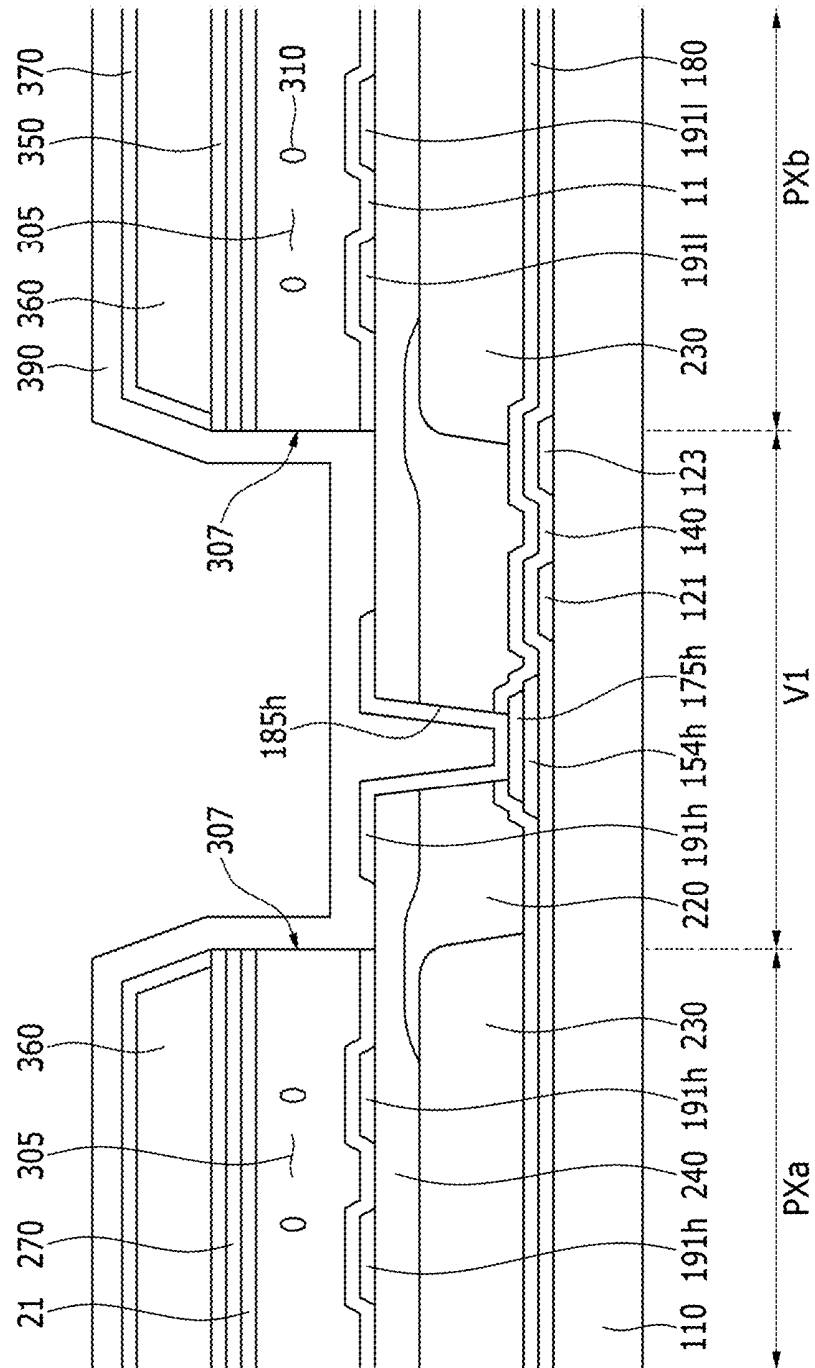


FIG. 8

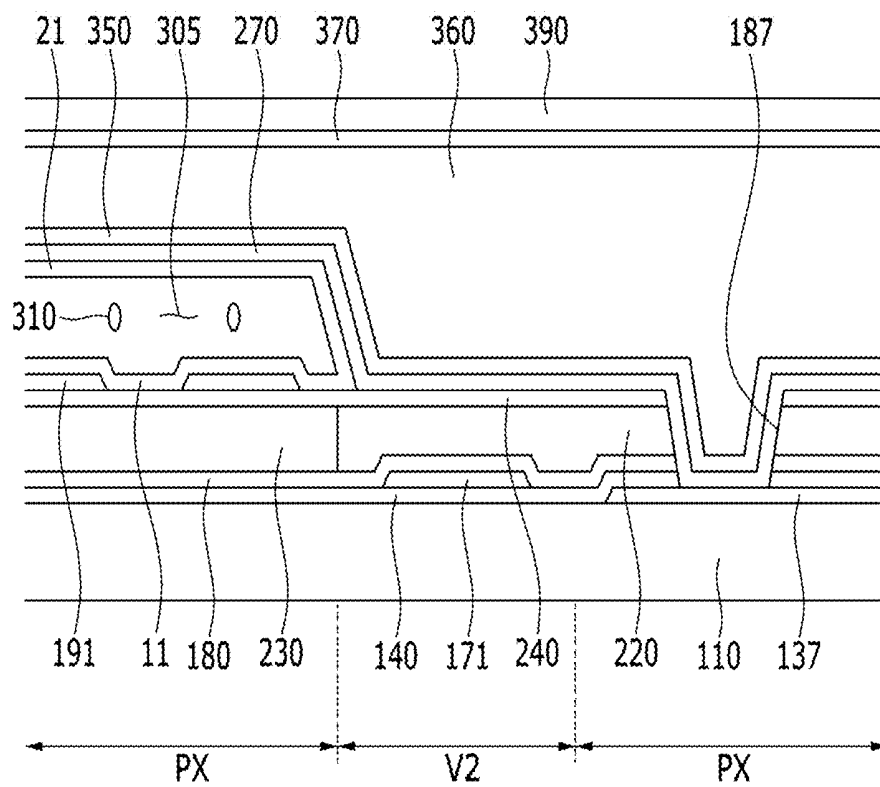
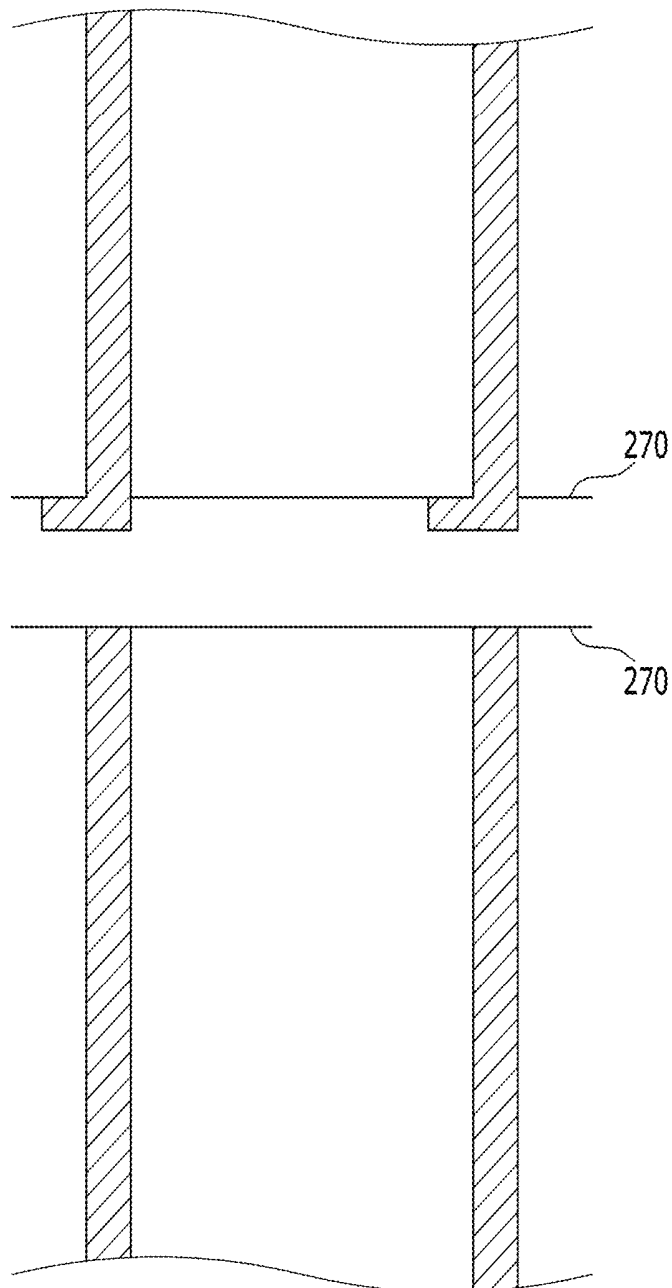


FIG. 9



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## DISPLAY DEVICE

### CROSS-REFERENCE TO RELATED APPLICATION

This application claims priority to and the benefit of Korean Patent Application No. 10-2014-0044981 filed in the Korean Intellectual Property Office on Apr. 15, 2014, the entire contents of which are incorporated herein by reference.

### BACKGROUND

#### (a) Technical Field

The present invention relates to a display device, and more particularly, to a display device capable of reducing common electrode resistance.

#### (b) Description of the Related Art

A liquid crystal display, which is one of the most common types of flat panel displays currently in use, includes two sheets of display panels with field generating electrodes such as a pixel electrode, a common electrode, and the like, and a liquid crystal layer interposed therebetween. The liquid crystal display generates an electric field in the liquid crystal layer by applying a voltage to the field generating electrodes to determine alignment of liquid crystal molecules through the generated electric field and control polarization of incident light, thereby displaying images.

Two sheets of display panels that make up the liquid crystal display may include a thin film transistor array panel and an opposing display panel. In the thin film transistor array panel, a gate line transferring a gate signal and a data line transferring a data signal are formed to cross each other, and a thin film transistor connected with the gate line and the data line, a pixel electrode connected with the thin film transistor, and the like may be formed. In the opposing display panel, a light blocking member, a color filter, a common electrode, and the like may be formed. In some cases, the light blocking member, the color filter, and the common electrode may be formed on the thin film transistor array panel.

However, in a liquid crystal display in the related art, two sheets of substrates are necessarily used, and respective constituent elements are formed on the two sheets of substrates, and as a result, there are problems in that the display device is heavy and thick, has high cost, and has a long processing time.

The above information disclosed in this Background section is only for enhancement of understanding of the background of the invention and therefore it may contain information that does not form the prior art that is already known in this country to a person of ordinary skill in the art.

### SUMMARY

The inventive concept disclosed herein provides a display device having advantages of reducing the weight, thickness, cost, and processing time by manufacturing the display device by using no more than one substrate.

Further, the inventive concept provides a display device having advantages of preventing a cross talk that is generated by the high resistance of a common electrode formed in a line shape.

In one aspect, the inventive concept provides a display device including: a substrate; a gate line, a data line, and a storage electrode line formed on the substrate; a thin film transistor connected to the gate line and the data line; a pixel electrode connected with the thin film transistor; a common electrode formed on the pixel electrode; a plurality of microcavities between the common electrode and the pixel elec-

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trode; a roof layer formed on the common electrode; a liquid crystal layer in the microcavity; and an encapsulation layer formed on the roof layer to seal the microcavity, wherein the common electrode is connected with the storage electrode line at a position adjacent to the data line, spaced apart from the microcavities.

The microcavities may be disposed in a matrix form, and the display device may further include first valleys positioned between the microcavities which are adjacent to each other in a column direction and second valleys positioned between the microcavities which are adjacent to each other in a row direction.

The common electrode may be connected with the storage electrode line at the second valley.

The data line may include a first data line and a second data line, and the first data line and the second data line may be positioned at both edges of the second valley, respectively.

The display device may further include an insulating layer formed between the storage electrode line and the common electrode, a contact hole extending through the insulating layer to at least a part of the storage electrode line positioned between the first data line and the second data line, wherein the common electrode may be connected with the storage electrode line through the contact hole.

The contact hole may be formed between the first data line and the second data line without reaching the first data line or the second data line.

The thin film transistor may include a first thin film transistor and a second thin film transistor, the pixel electrode may include a first subpixel electrode and a second subpixel electrode, the first thin film transistor may be connected with the first data line and the first subpixel electrode, and the second thin film transistor may be connected with the second data line and the second subpixel electrode.

A data voltage applied to the second data line may be different from a data voltage applied to the first data line.

The common electrode may be connected with the storage electrode line in the first valley.

The common electrode may be attached to the substrate in the first valley and the second valley.

A portion of the common electrode that is attached to the substrate may have an L-shape.

The display device may further include a capacitive electrode protruding from the storage electrode line, in which the common electrode may be directly connected with the capacitive electrode.

The display device may further include an insulating layer formed between the storage electrode line and the common electrode, and a contact hole extending through the insulating layer to at least a part of the capacitive electrode, wherein the common electrode may be connected with the capacitive electrode through the contact hole.

According to the exemplary embodiment of the present invention, the common electrode is connected with the storage electrode line, thereby reducing a resistance of the common electrode.

### BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a plan view illustrating a display device according to an exemplary embodiment of the present inventive concept.

FIG. 2 is an equivalent circuit diagram of one pixel of the display device according to an exemplary embodiment of the present inventive concept.

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FIG. 3 is a layout view illustrating a part of the display device according to an exemplary embodiment of the present inventive concept.

FIG. 4 is a cross-sectional view illustrating the display device taken along line IV-IV according to an exemplary embodiment of the present inventive concept.

FIG. 5 is a cross-sectional view illustrating the display device taken along line V-V according to an exemplary embodiment of the present inventive concept.

FIG. 6 is a plan view illustrating one pixel of a display device according to an exemplary embodiment of the inventive concept.

FIG. 7 is a cross-sectional view illustrating a part of the display device of FIG. 6 taken along line VII-VII according to the exemplary embodiment of the inventive concept.

FIG. 8 is a cross-sectional view illustrating a part of the display device of FIG. 6 taken along line VIII-VIII according to an exemplary embodiment of the inventive concept.

FIG. 9 is a layout view illustrating a common electrode of the display device according to an exemplary embodiment of the inventive concept.

#### DETAILED DESCRIPTION OF THE EMBODIMENTS

The inventive concept will be described more fully hereinafter with reference to the accompanying drawings, in which exemplary embodiments are shown. As those skilled in the art would realize, the described embodiments may be modified in various different ways, all without departing from the spirit or scope of the inventive concept.

In the drawings, the thickness of layers, films, panels, regions, etc., are exaggerated for clarity. Like reference numerals designate like elements throughout the specification. It will be understood that when an element such as a layer, film, region, or substrate is referred to as being "on" another element, it can be directly on the other element or intervening elements may also be present. In contrast, when an element is referred to as being "directly on" another element, there are no intervening elements present.

First, a display device according to an exemplary embodiment of the inventive concept will be schematically described below with reference to FIG. 1.

FIG. 1 is a plan view illustrating a display device according to an exemplary embodiment of the inventive concept.

A display device according to the exemplary embodiment of the present invention includes a substrate 110 made of a material such as glass or plastic.

A microcavity 305 covered by a roof layer 360 is formed on the substrate 110. The roof layers 360 extend in a row direction, and a plurality of microcavities 305 is formed below one roof layer 360.

The microcavities 305 may be disposed in a matrix form. First valleys V1 are positioned between the microcavities 305 adjacent to each other in a column direction, and second valleys V2 are positioned between the microcavities 305 adjacent to each other in a row direction.

The plurality of roof layers 360 are separated from each other with the first valleys V1 therebetween. The microcavity 305 is not covered by the roof layer 360, but may be exposed outside at a portion contacting the first valley V1. This is called injection holes 307a and 307b.

The injection holes 307a and 307b are formed at both edges of the microcavity 305. The injection holes 307a and 307b are configured by a first injection hole 307a and a second injection hole 307b, the first injection hole 307a is formed to expose a side of a first edge of the microcavity 305, and the

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second injection hole 307b is formed to expose a side of a second edge of the microcavity 305. The side of the first edge and the side of the second edge of the microcavity 305 face each other.

Each roof layer 360 is formed to be separated from the substrate 110 between the adjacent second valleys V2 to form the microcavity 305. That is, the roof layer 360 is formed to cover all sides of the microcavity 305 except for the sides adjacent to the first edge and the second edge where the injection holes 307a and 307b are formed.

The structure of the display device according to the exemplary embodiment described above is just exemplary, and may be modified in various ways. For example, the layout of the microcavities 305, the first valleys V1, and the second valleys V2 may be adjusted. The plurality of roof layers 360 may be connected to each other at an area above the first valleys V1 and separated from the substrate 110 at the second valley V2, thus connecting the adjacent microcavities 305 to each other.

Hereinafter, one pixel of the display device according to the exemplary embodiment of the inventive concept will be schematically described below with reference to FIG. 2.

FIG. 2 is an equivalent circuit diagram of one pixel of the display device according to the exemplary embodiment of the inventive concept.

The display device according to the exemplary embodiment includes a plurality of signal lines 121, 171h, and 171l, and pixels PX connected thereto. Although not illustrated, a plurality of pixels PX may be disposed in a matrix form which includes a plurality of pixel rows and a plurality of pixel columns.

Each pixel PX may include a first subpixel PXa and a second subpixel PXb. The first subpixel PXa and the second subpixel PXb may be vertically disposed. In this case, the first valley V1 may be positioned between the first subpixel PXa and the second subpixel PXb in a pixel row direction, and a second valley V2 may be positioned between the plurality of pixel columns.

The signal lines 121, 171h, and 171l include a gate line 121 transferring a gate signal, and a first data line 171h and a second data line 171l transferring different data voltages.

A first thin film transistor Qh connected to the gate line 121 and the first data line 171h is formed, and a second thin film transistor Ql connected to the gate line 121 and the second data line 171l is formed.

In the first subpixel PXa, a first liquid crystal capacitor Clch connected to a first thin film transistor Qh is formed, and in the second subpixel PXb, a second liquid crystal capacitor Clcl connected to a second thin film transistor Ql is formed.

A first terminal of the first thin film transistor Qh is connected to the gate line 121, a second terminal is connected to the first data line 171h, and a third terminal is connected to the first liquid crystal capacitor Clch.

A first terminal of the second thin film transistor Ql is connected to the gate line 121, a second terminal is connected to the second data line 171l, and a third terminal is connected to the second liquid crystal capacitor Clcl.

In an operation of a display device according to the exemplary embodiment, when a gate-on voltage is applied to the gate line 121, the first thin film transistor Qh and the second thin film transistor Ql connected thereto are turned on, and the first and second liquid crystal capacitors Clch and Clcl are charged by different data voltages transferred through the first and second data lines 171h and 171l. The data voltage transferred by the second data line 171l is lower than the data voltage transferred by the first data line 171h. Accordingly, the second liquid crystal capacitor Clcl is charged at a differ-

ent voltage (e.g., a lower voltage) than that of the first liquid crystal capacitor Clch, thereby improving side visibility. "Side visibility," as used herein, refers to how images look when the display panel is viewed at an angle, from a position that is off-center.

Hereinafter, a structure of one pixel of the display device according to the exemplary embodiment of the present invention will be described with reference to FIGS. 3 to 5.

FIG. 3 is a layout view illustrating one pixel of the display device according to the exemplary embodiment of the inventive concept, and FIG. 4 is a cross-sectional view illustrating the display device taken along line IV-IV according to the exemplary embodiment of the inventive concept. FIG. 5 is a cross-sectional view illustrating the display device taken along line V-V according to the exemplary embodiment of the inventive concept.

Referring to FIGS. 3 to 5, a gate line 121, a first gate electrode 124h, and a second gate electrode 124l which protrude from the gate line 121 are formed on the substrate 110.

The gate line 121 extends in a first direction and transfers a gate signal. The gate line 121 is positioned between two microcavities 305 which are adjacent to each other in a column direction. That is, the gate line 121 is positioned on the first valley V1. The first gate electrode 124h and the second gate electrode 124l protrude from the gate line 121, as shown in FIG. 3. The first gate electrode 124h and the second gate electrode 124l are connected with each other to form one protrusion. However, the present invention is not limited thereto, and the protruding form of the first gate electrode 124h and the second gate electrode 124l may be modified in various ways.

A storage electrode line 131, and storage electrodes 133 and 135 protruding from the storage electrode line 131 may be further formed on the substrate 110.

The storage electrode line 131 extends in a direction parallel to the gate line 121, and is formed to be spaced apart from the gate line 121. A predetermined voltage may be applied to the storage electrode line 131. The storage electrode 133 protruding above the storage electrode line 131 is formed to surround an edge of the first subpixel PXa. The storage electrode 135 protruding below the storage electrode line 131 is formed to be adjacent to the first gate electrode 124h and the second gate electrode 124l.

A gate insulating layer 140 is formed on the gate line 121, the first gate electrode 124h, the second gate electrode 124l, the storage electrode line 131, and the storage electrodes 133 and 135. The gate insulating layer 140 may be made of an inorganic insulating material such as silicon nitride (SiNx) and silicon oxide (SiOx). Further, the gate insulating layer 140 may be formed as a single layer or a multiple layer.

A first semiconductor 154h and a second semiconductor 154l are formed on the gate insulating layer 140. The first semiconductor 154h may be positioned on the first gate electrode 124h, and the second semiconductor 154l may be positioned on the second gate electrode 124l. The first semiconductor 154h may be formed even below the first data line 171h, and the second semiconductor 154l may be formed even below the second data line 171l. The first semiconductor 154h and the second semiconductor 154l may be made of amorphous silicon, polycrystalline silicon, metal oxide, and the like.

An ohmic contact member (not illustrated) may be further formed on each of the first semiconductor 154h and the second semiconductor 154l. The ohmic contact member may be made of silicide or a material such as n+ hydrogenated amorphous silicon in which n-type impurity is doped at a high concentration.

On the first semiconductor 154h, the second semiconductor 154l and the gate insulating layer 140, the first data line 171h, the second data line 171l, the first source electrode 173h, the first drain electrode 175h, the second source electrode 173l, and the second drain electrode 175l are formed.

The first data line 171h and the second data line 171l transfer data signals and extend in a second direction to cross the gate line 121 and the storage electrode line 131. The data line 171 is positioned between two microcavities 305 which are adjacent to each other in a row direction. That is, the data line 171 is positioned at the second valley V2. The first data line 171h and the second data line 171l are positioned at both edges of the second valley V2, respectively.

The first data line 171h and the second data line 171l transfer different data voltages. The data voltage transferred by the second data line 171l is lower than the data voltage transferred by the first data line 171h.

The first source electrode 173h protrudes above the first gate electrode 124h from the first data line 171h, and the second source electrode 173l protrudes above the second gate electrode 124l from the second data line 171l. Each of the first drain electrode 175h and the second drain electrode 175l includes one wide end portion and the other rod-shaped end portion. The wide end portions of the first drain electrode 175h and the second drain electrode 175l overlap with the storage electrode 135 protruding below the storage electrode line 131. The rod-shaped end portions of the first drain electrode 175h and the second drain electrode 175l are partially surrounded by the first source electrode 173h and the second source electrode 173l, respectively.

The first and second gate electrodes 124h and 124l, the first and second source electrodes 173h and 173l, and the first and second drain electrodes 175h and 175l form first and second thin film transistors (TFTs) Qh and Ql together with the first and second semiconductors 154h and 154l, respectively, and a channel of the thin film transistor is formed in each of the semiconductors 154h and 154l between each of the source electrodes 173h and 173l and each of the drain electrodes 175h and 175l.

A passivation layer 180 is formed on the first data line 171h, the second data line 171l, the first source electrode 173h, the first drain electrode 175h, the first semiconductor 154h exposed between the first source electrode 173h and the first drain electrode 175h, the first semiconductor 154h, the second source electrode 173l, the second drain electrode 175l, and the second semiconductor 154l exposed between the second source electrode 173l and the second drain electrode 175l. The passivation layer 180 may be made of an organic insulating material or an inorganic insulating material, and may be formed as a single layer or a multiple layer.

A color filter 230 in each pixel PX is formed on the passivation layer 180.

Each color filter 230 may display one of the primary colors such as three primary colors of red, green and blue. The color filter 230 is not limited to the three primary colors of red, green and blue, but may display cyan, magenta, yellow, and white-based colors. The color filter 230 may not be formed at the first valley V1.

A light blocking member 220 is formed in a region between the adjacent color filters 230. The light blocking member 220 is formed on a boundary of the pixel PX and the thin film transistors Qh and Ql to prevent light leakage. That is, the light blocking member 220 may be formed at the first valley V1 and the second valley V2. The color filter 230 and the light blocking member 220 may overlap with each other in a partial region.

A first insulating layer **240** may be further formed on the color filter **230** and the light blocking member **220**. The first insulating layer **240** may be made of an organic insulating material, and may serve to planarize the color filters **230**.

A second insulating layer **250** may be further formed on the first insulating layer **240**. The second insulating layer **250** may be made of an inorganic insulating material, and may serve to protect the color filters **230** and the first insulating layer **240**.

In the passivation layer **180**, the first insulating layer **240**, and the second insulating layer **250**, a first contact hole **181h** exposing the wide end portion of the first drain electrode **175h** is formed, and a second contact hole **181l** exposing the wide end portion of the second drain electrode **175l** are formed.

A pixel electrode **191** is formed on the second insulating layer **250**. The pixel electrode **191** may be made of a transparent metal material such as indium tin oxide (ITO) and indium zinc oxide (IZO).

The pixel electrode **191** includes a first subpixel electrode **191h** and a second subpixel electrode **191l** which are separated from each other with the gate line **121** and the storage electrode line **131** therebetween. The first subpixel electrode **191h** and the second subpixel electrode **191l** are disposed above and below the pixel PX based on the gate line **121** and the storage electrode line **131**. That is, the first subpixel electrode **191h** and the second subpixel electrode **191l** are separated from each other with the first valley V1 therebetween, the first subpixel electrode **191h** is positioned in the first subpixel PXa, and the second subpixel electrode **191l** is positioned in the second subpixel PXb.

The first subpixel electrode **191h** is connected with the first drain electrode **175h** through the first contact hole **181h**, and the second subpixel electrode **191l** is connected to the second drain electrode **175l** through the second contact hole **181l**. Accordingly, when the first thin film transistor Qh and the second thin film transistor Ql are turned on, the first subpixel electrode **191h** and the second subpixel electrode **191l** receive different data voltages from the first drain electrode **175h** and the second drain electrode **175l**, respectively. An electric field may be generated between the pixel electrodes **191h**, **191l** and the common electrode **270**.

The general shape of each of the first subpixel electrode **191h** and the second subpixel electrode **191l** is a quadrangle, and the first subpixel electrode **191h** and the second subpixel electrode **191l** include cross stems including horizontal stems **193h** and **193l** and vertical stems **192h** and **192l** crossing the horizontal stems **193h** and **193l**, respectively. Further, each of the first subpixel electrode **191h** and the second subpixel electrode **191l** includes a plurality of minute branches **194h** and **194l**.

The pixel electrode **191** is divided into four subregions by the horizontal stems **193h** and **193l** and the vertical stems **192h** and **192l**. The minute branches **194h** and **194l** obliquely extend from the horizontal stems **193h** and **193l** and the vertical stems **192h** and **192l**, and the extending direction may form an angle of approximately 45 degrees or 135 degrees with the gate line **121** or the horizontal stems **193h** and **193l**. Further, extending directions of the minute branches **194h** and **194l** of the two adjacent subregions may be perpendicular to each other.

In the exemplary embodiment, the first subpixel electrode **191h** and the second subpixel electrode **191l** may further include outer stems surrounding outsides of the first subpixel PXa and the second subpixel PXb.

The layout form of the pixel, the structure of the thin film transistor, and the shape of the pixel electrode described

above are just exemplary, and the inventive concept is not limited thereto and may be modified in various ways.

The common electrode **270** is formed on the pixel electrode **191** so as to be spaced apart from the pixel electrode **191** at a predetermined distance. The microcavity **305** is formed between the pixel electrode **191** and the common electrode **270**. That is, the microcavity **305** is surrounded by the pixel electrode **191** and the common electrode **270**. The common electrode **270** is formed in a row direction, and formed on the microcavity **305** and at the second valley V2. The common electrode **270** is formed to cover an upper surface and a side of the microcavity **305**. A width and an area of the microcavity **305** may be variously modified according to a size and a resolution of the display device.

In each pixel PX, the common electrode **270** is formed to be separated from the substrate **110** and thus the microcavity **305** is formed, but the common electrode **270** is formed to be attached to the substrate **110** in the second valley V2. At the second valley V2, the common electrode **270** is formed directly on the second insulating layer **250**. No space is formed between the second insulating layer **250** and the common electrode **270**.

The storage electrode line **131** and the common electrode **270** are overlapped with each other. Insulating layers such as the gate insulating layer **140**, the passivation layer **180**, the light blocking member **220**, the first insulating layer **240**, and the second insulating layer **250** are formed between the storage electrode line **131** and the common electrode **270**. A third contact hole **186** is formed in the insulating layers. The third contact hole **186** passing through the gate insulating layer **140**, the passivation layer **180**, the light blocking member **220**, the first insulating layer **240**, and the second insulating layer **250** is formed to extend to at least a part of the storage electrode line **131** (see FIG. 5). The third contact hole **186** is positioned at the second valley V2, and positioned between the first data line **171h** and the second data line **171l**. The third contact hole **186** does not extend to the first data line **171h** and the second data line **171l**.

The common electrode **270** is connected with the storage electrode line **131** through the third contact hole **186**. The common electrode **270** is connected with the storage electrode line **131** at a position adjacent to the data line **171**. The common electrode **270** is connected with the storage electrode line **131** between the first data line **171h** and the second data line **171l**. That is, the common electrode **270** is connected with the storage electrode line **131** at the second valley V2. In this case, since the data line **171** is not exposed by the third contact hole **186**, the data line **171** is not connected with the common electrode **270**.

In the exemplary embodiment, a plurality of common electrodes **270** is formed in a row direction. Accordingly, the resistance of the common electrode **270** may be increased in comparison with a case where the common electrode **270** is entirely formed on the substrate **110** as one planar electrode. In the exemplary embodiment, the resistance of the common electrode **270** may be reduced by connecting the common electrode **270** with the storage electrode line **131**. In this case, the same common voltage may be applied to the storage electrode line **131** and the common electrode **270**.

The common electrode **270** may be made of a transparent metal material such as indium tin oxide (ITO) and indium zinc oxide (IZO). A predetermined voltage may be applied to the common electrode **270**, and an electric field may be generated between the pixel electrode **191** and the common electrode **270**.

A first alignment layer **11** is formed on the pixel electrode **191**. The first alignment layer **11** may also be formed directly on the second insulating layer **250** which is not covered by the pixel electrode **191**.

A second alignment layer **21** is formed below the common electrode **270** to face the first alignment layer **11**.

The first alignment layer **11** and the second alignment layer **21** may be formed by vertical alignment layers, and made of alignment materials such as polyamic acid, polysiloxane, and polyimide. The first and second alignment layers **11** and **21** may be connected to each other at a side wall of the edge of the microcavity **305**.

A liquid crystal layer configured by liquid crystal molecules **310** is formed in the microcavity **305** positioned between the pixel electrode **191** and the common electrode **270**. The liquid crystal molecules **310** have negative dielectric anisotropy, and may stand up in a vertical direction to the substrate **110** while the electric field is not applied. That is, vertical alignment may be performed.

The first subpixel electrode **191h** and the second subpixel electrode **191l** to which the data voltages are applied generate an electric field together with the common electrode **270** to determine the alignment directions of the liquid crystal molecules **310** positioned in the microcavity **305** between the two electrodes **191** and **270**. Luminance of light passing through the liquid crystal layer varies according to the alignment directions of the liquid crystal molecules **310**.

A third insulating layer **350** may be further formed on the common electrode **270**. The third insulating layer **350** may be made of an inorganic insulating material such as silicon nitride (SiNx) and silicon oxide (SiOx), and may be omitted if necessary.

A roof layer **360** is formed on the third insulating layer **350**. The roof layer **360** may be made of an organic material. The roof layer **360** is formed in a row direction, and formed on the microcavity **305** and at the second valley **V2**. The roof layer **360** is formed to cover an upper surface and a side of the microcavity **305**. The roof layer **360** is hardened by a curing process to serve to maintain the shape of the microcavity **305**. The roof layer **360** is formed to be spaced apart from the pixel electrode **191** with the microcavity **305** therebetween.

The common electrode **270** and the roof layer **360** are formed to expose the side of the edge of the microcavity **305**, and portions where the microcavity **305** is not covered by the common electrode **270** and the roof layer **360** are called injection holes **307a** and **307b**. The injection holes **307a** and **307b** include a first injection hole **307a** exposing the side of the first edge of the microcavity **305** and a second injection hole **307b** exposing the side of the second edge of the microcavity **305**. The first edge and the second edge face each other, and sometimes, the first edge may be an upper edge of the microcavity **305**, and the second edge may be a lower edge of the microcavity **305**. The injection holes **307a** and **307b** expose edge sides of the microcavity **305** adjacent to the first valley **V1**. Since the microcavity **305** is exposed by the injection holes **307a** and **307b**, an aligning agent, a liquid crystal material, or the like may be injected into the microcavity **305** through the injection holes **307a** and **307b**.

In the exemplary embodiment, the common electrode **270** is connected with the storage electrode line **131**. In this case, when a position where the common electrode **270** and the storage electrode line **131** are connected with each other is at a center of the injection holes **307a** and **307b**, injection of an aligning agent or a liquid crystal material may be disturbed. In the exemplary embodiment of the inventive concept, since the common electrode **270** and the storage electrode line **131** are connected with each other at a position beyond the injection

holes **307a** and **307b**, the injection of an aligning agent or a liquid crystal material may be easily performed. Further, in the exemplary embodiment, there is minimal loss of an aperture ratio by the connection of the common electrode **270** and the storage electrode line **131**.

A fourth insulating layer **370** may be further formed on the roof layer **360**. The fourth insulating layer **370** may be made of an inorganic insulating material such as silicon nitride (SiNx) and silicon oxide (SiOx). The fourth insulating layer **370** may be formed to cover an upper surface and a side of the roof layer **360**. The fourth insulating layer **370** serves to protect the roof layer **360** made of an organic material, and may be omitted if necessary.

An encapsulation layer **390** is formed on the fourth insulating layer **370**. The encapsulation layer **390** is formed to cover the injection holes **307a** and **307b** by which a part of the microcavity **305** is exposed. That is, the encapsulation layer **390** may seal the microcavity **305** so that the liquid crystal molecules **310** formed in the microcavity **305** are not discharged outside. Since the encapsulation layer **390** contacts the liquid crystal molecules **310**, the encapsulation layer **390** may be made of a material which does not react with liquid crystal molecules **310**. For example, the encapsulation layer **390** may be made of parylene and the like.

The encapsulation layer **390** may be formed by a multi-layer such as a double layer and a triple layer. The double layer is configured by two layers made of different materials. The triple layer is configured by three layers, and materials of adjacent layers are different from each other. For example, the encapsulation layer **390** may include a layer made of an organic insulating material and a layer made of an inorganic insulating material.

Although not illustrated, polarizers may be further formed on upper and lower sides of the display device. The polarizers may be configured by a first polarizer and a second polarizer. The first polarizer may be attached onto the lower side of the substrate **110**, and the second polarizer may be attached onto the encapsulation layer **390**.

Next, one pixel of the display device according to the exemplary embodiment will be described below with reference to FIGS. **6** to **8**.

Since the display device according to an exemplary embodiment of FIGS. **6** to **8** is almost the same as the display device according to the exemplary embodiment of FIGS. **1** to **5**, any redundant description is omitted.

FIG. **6** is a plan view illustrating one pixel of the display device according to an exemplary embodiment of the inventive concept, FIG. **7** is a cross-sectional view illustrating a part of the display device taken along line VII-VII of FIG. **6** according to the exemplary embodiment, and FIG. **8** is a cross-sectional view illustrating a part of the display device taken along line VIII-VIII of FIG. **6** according to the exemplary embodiment.

Referring to FIGS. **6** to **8**, a plurality of gate conductors including a plurality of gate lines **121**, a plurality of step-down gate lines **123**, and a plurality of storage electrode lines **131** is formed on the substrate **110**.

The gate line **121** and the step-down gate line **123** mainly extend in a horizontal direction to transfer gate signals. The gate conductor further includes a first gate electrode **124h** and a second gate electrode **124l** protruding upward and downward from the gate line **121**, and further includes a third gate electrode **124c** protruding upward from the step-down gate line **123**. The first gate electrode **124h** and the second gate electrode **124l** are connected with each other to form one

protrusion. In this case, the protruding form of the first, second, and third gate electrodes **124h**, **124l**, and **124c** may be modified.

The storage electrode line **131** mainly extends in a horizontal direction and transfers a predetermined voltage such as a common voltage **Vcom**. The storage electrode line **131** includes storage electrodes **129** protruding upward and downward, a pair of vertical portions **134** extending downward to be substantially vertical to the gate line **121**, and a horizontal portion **127** connecting ends of the pair of vertical portions **134**. The horizontal portion **127** includes a capacitor electrode **137** expanded downward.

A gate insulating layer **140** is formed on the gate conductor **121**, **123**, **124h**, **124l**, **124c**, and **131**. The gate insulating layer **140** may be made of an inorganic insulating material such as silicon nitride (**SiNx**) and silicon oxide (**SiOx**). Further, the gate insulating layer **140** may be formed as a single layer or a multiple layer.

A first semiconductor **154h**, a second semiconductor **154l**, and a third semiconductor **154c** are formed on the gate insulating layer **140**. The first semiconductor **154h** may be positioned on the first gate electrode **124h**, the second semiconductor **154l** may be positioned on the second gate electrode **124l**, and the third semiconductor **154c** may be positioned on the third gate electrode **124c**. The first semiconductor **154h** and the second semiconductor **154l** may connect to each other, and the second semiconductor **154l** and the third semiconductor **154c** may connect to each other. Further, the first semiconductor **154h** may extend to the lower portion of the data line **171**. The first to third semiconductors **154h**, **154l**, and **154c** may be made of amorphous silicon, polycrystalline silicon, metal oxide, and the like.

Ohmic contact members (not illustrated) may be further formed on the first to third semiconductors **154h**, **154l**, and **154c**, respectively. The ohmic contact member may be made of silicide or a material such as **n+** hydrogenated amorphous silicon in which **n**-type impurity is doped at a high concentration.

A data conductor including a data line **171**, a first source electrode **173h**, a second source electrode **173l**, a third source electrode **173c**, a first drain electrode **175h**, a second drain electrode **175l**, and a third drain electrode **175c** is formed on the first to third semiconductors **151h**, **154l**, and **154c**.

The data line **171** transfers a data signal and mainly extends in a vertical direction to cross the gate line **121** and the step-down gate line **123**.

The first source electrode **173h** and the second source electrode **173l** are connected with the data line **171**, and formed on the first gate electrode **124h** and the second gate electrode **124l**, respectively. The first source electrode **173h** and the second source electrode **173l** are connected with each other.

Each of the first drain electrode **175h** and the second drain electrode **175l** includes one wide end portion and the other rod-shaped end portion. The rod-shaped end portions of the first drain electrode **175h** and the second drain electrode **175l** are partially surrounded by the first source electrode **173h** and the second source electrode **173l**, respectively. One wide end portion of the second drain electrode **175l** extends to form a third drain electrode **175c** which is bent in a 'U'-lettered shape.

The third source electrode **173c** includes a wide end portion and a rod-shaped end portion. A wide end portion **177c** of the third source electrode **173c** overlaps with the capacitive electrode **137** to form a step-down capacitor **Cstd**, and the rod-shaped end portion is partially surrounded by the third drain electrode **175c**.

The first gate electrode **124h**, the first source electrode **173h**, and the first drain electrode **175h** form a first thin film transistor **Qh** together with the first semiconductor **154h**, the second gate electrode **124l**, the second source electrode **173l**, and the second drain electrode **175l** form a second thin film transistor **Ql** together with the second semiconductor **154l**, and the third gate electrode **124c**, the third source electrode **173c**, and the third drain electrode **175c** form the third thin film transistor **Qc** together with the third semiconductor **154c**.

The first semiconductor **154h**, the second semiconductor **154l**, and the third semiconductor **154c** may be connected to each other, and may have substantially the same planar shape as the data conductor **171**, **173h**, **173l**, **173c**, **175h**, **175l**, and **175c** and the ohmic contact members therebelow, except for channel regions between the source electrodes **173h**, **173l**, and **173c** and the drain electrodes **175h**, **175l**, and **175c**.

In the first semiconductor **154h**, a portion that is not covered by the first source electrode **173h** and the first drain electrode **175h** is disposed between the first source electrode **173h** and the first drain electrode **175h**. In the second semiconductor **154l**, an exposed portion which is not covered by the second source electrode **173l** and the second drain electrode **175l** is disposed between the second source electrode **173l** and the second drain electrode **175l**. In addition, in the third semiconductor **154c**, a portion that is not covered by the third source electrode **173c** and the third drain electrode **175c** is disposed between the third source electrode **173c** and the third drain electrode **175c**.

A passivation layer **180** is formed on the data conductor **171**, **173h**, **173l**, **173c**, **175h**, **175l**, and **175c** and the semiconductors **154h**, **154l**, and **154c** exposed between the respective source electrodes **173h/173l/173c** and the respective drain electrodes **175h/175l/175c**. The passivation layer **180** may be made of an organic insulating material or an inorganic insulating material, and may be formed as a single layer or multiple layers.

A color filter **230** in each pixel **PX** is formed on the passivation layer **180**. Each color filter **230** may display one of the primary colors such as three primary colors of red, green and blue. The color filter **230** is not limited to the three primary colors of red, green and blue, but may display cyan, magenta, yellow, and white-based colors. Unlike the embodiments illustrated above, the color filter **230** may extend in a column direction along a space between the adjacent data lines **171**.

A light blocking member **220** is formed in a region between the adjacent color filters **230**. The light blocking member **220** is formed on a boundary of the pixel **PX** and the thin film transistor to prevent light leakage. The color filter **230** is formed in each of the first subpixel **PXa** and the second subpixel **PXb**, and the light blocking member **220** may be formed between the first subpixel **PXa** and the second subpixel **PXb**.

The light blocking member **220** extends along the gate line **121** and the step-down gate line **123** to be expanded upward and downward, and includes a horizontal light blocking member **220a** which covers regions where the first thin film transistor **Qh**, the second thin film transistor **Ql**, and the third thin film transistor **Qc** are positioned, and a vertical light blocking member **220b** which extends along the data line **171**. That is, the horizontal light blocking member **220a** may be formed at the first valley **V1**, and the vertical light blocking member **220b** may be formed at the second valley **V2**. The color filter **230** and the light blocking member **220** may overlap with each other in a partial region.

A first insulating layer **240** may be further formed on the color filter **230** and the light blocking member **220**. The first insulating layer **240** is made of an organic insulating material,

and may serve as a planarization layer for a step formed between the color filter 230 and the light blocking member 220. Further, the first insulating layer 240 may be made of an inorganic insulating material such as silicon nitride (SiNx) and silicon oxide (SiOx). The first insulating layer 240 may be omitted in some cases.

In the first insulating layer 240, the light blocking member 220, and the passivation layer 180, a plurality of first contact holes 185h and a plurality of second contact holes 185l, which expose the wide end portion of the first drain electrode 175h and the wide end portion of the second drain electrode 175l, respectively, are formed.

A pixel electrode 191 is formed on the first insulating layer 240. The pixel electrode 191 may be made of a transparent metal material such as indium tin oxide (ITO) and indium zinc oxide (IZO).

The pixel electrode 191 includes a first subpixel electrode 191h and a second subpixel electrode 191l which are separated from each other with the gate line 121 and the step-down gate line 123 therebetween, and disposed above and below the pixel PX based on the gate line 121 and the step-down gate line 123 to be adjacent to each other in a column direction. That is, the first subpixel electrode 191h and the second subpixel electrode 191l are separated from each other with the first valley V1 therebetween, the first subpixel electrode 191h is positioned in the first subpixel PXa, and the second subpixel electrode 191l is positioned in the second subpixel PXb.

The first subpixel electrode 191h and the second subpixel electrode 191l are connected with the first drain electrode 175h and the second drain electrode 175l through the first contact hole 185h and the second contact hole 185l, respectively. Accordingly, when the first thin film transistor Qh and the second thin film transistor Ql are turned on, the first subpixel electrode 191h and the second subpixel electrode 191l receive data voltages from the first drain electrode 175h and the second drain electrode 175l.

Each of the subpixel electrode 191h and the second subpixel electrode 191l is generally quadrangular in shape, and the first subpixel electrode 191h and the second subpixel electrode 191l include cross stems including horizontal stems 193h and 193l and vertical stems 192h and 192l crossing the horizontal stems 193h and 193l, respectively. Further, the first subpixel electrode 191h and the second subpixel electrode 191l include a plurality of minute branches 194h and 194l, and protrusions 197h and 197l protruding downward or upward from edge sides of the subpixel electrodes 194h and 194l, respectively.

The pixel electrode 191 is divided into four subregions by the horizontal stems 193h and 193l and the vertical stems 192h and 192l. The minute branches 194h and 194l obliquely extend from the horizontal stems 193h and 193l and the vertical stems 192h and 192l and the extending direction may form an angle of approximately 45 degrees or 135 degrees with the gate line 121 or the horizontal stems 193h and 193l. Further, extending directions of the minute branches 194h and 194l of the two adjacent subregions may be perpendicular to each other.

In the exemplary embodiment, the first subpixel electrode 191h further includes an outer stem surrounding the outside, and the second subpixel electrode 191l further includes horizontal portions positioned at an upper end and a lower end, and left and right vertical portions 198 positioned at the left and right sides of the first subpixel electrode 191h. The left and right vertical portions 198 may prevent capacitive coupling, that is, coupling between the data line 171 and the first subpixel electrode 191h.

The layout form of the pixel, the structure of the thin film transistor, and the shape of the pixel electrode described above are just exemplified, and the present invention is not limited thereto and may be variously modified.

The common electrode 270 is formed on the pixel electrode 191 so as to be spaced apart from the pixel electrode 191 at a predetermined distance. The microcavity 305 is formed between the pixel electrode 191 and the common electrode 270. That is, the microcavity 305 is surrounded by the pixel electrode 191 and the common electrode 270. The common electrode 270 is formed in a row direction, and formed on the microcavity 305 and at the first valley V1 and the second valley V2. The common electrode 270 is formed to cover an upper surface and a side of the microcavity 305. A width and an area of the microcavity 305 may be variously modified according to a size and a resolution of the display device.

In each pixel PX, the common electrode 270 is formed to be separated from the substrate 110 and thus the microcavity 305 is formed, but the common electrode 270 is formed to be attached to the substrate 110 at the first valley V1 and the second valley V2. At the second valley V2, the common electrode 270 is formed directly on the first insulating layer 240. A space is not formed between the first insulating layer 240 and the common electrode 270.

FIG. 9 depicts the common electrode 270 of a display device according to an exemplary embodiment of the present inventive concept. A portion of the common electrode 270 that is attached to the substrate 110 is indicated by shading.

A planar shape of the portion where the common electrode 270 is attached to the substrate 110 has an L-shape. The portion where the common electrode 270 is attached to the substrate 110 includes a portion that overlaps the data line 171 and a portion overlapping the capacitive electrode 137, and the two portions are connected with each other.

The common electrode 270 overlaps the capacitive electrode 137. Insulating layers such as the gate insulating layer 140, the passivation layer 180, the light blocking member 220, and the first insulating layer 240 are formed between the capacitive electrode 137 and the common electrode 270. A fourth contact hole 187 is formed in the insulating layers. The fourth contact hole 187 passing through the gate insulating layer 140, the passivation layer 180, the light blocking member 220, and the first insulating layer 240 is formed to extend to at least a part of the capacitive electrode 137. The fourth contact hole 187 is positioned at the first valley V1, and adjacent to the data line 171. The fourth contact hole 187 does not expose the data line 171 and the third source electrode 173c.

The common electrode 270 is connected with the capacitive electrode 137 through the fourth contact hole 187. The common electrode 270 is connected with the capacitive electrode 137 at a position adjacent to the data line 171. The common electrode 270 is connected with the capacitive electrode 137 at the first valley V1. Since the capacitive electrode 137 is connected with the storage electrode line 131, the common electrode 270 is electrically connected to the storage electrode line 131. The common electrode 270 directly contacts the capacitive electrode 137, and the common electrode 270 is indirectly connected with the storage electrode line 131 through the capacitive electrode 137. In this case, since the fourth contact hole 187 does not extend to the data line 171 and the third source electrode 173c, the data line 171 and the third source electrode 173c are not connected with the common electrode 270.

In the exemplary embodiment, a plurality of common electrodes 270 is formed in a row direction. Accordingly, the resistance of the common electrode 270 may be increased in

comparison with a case where the common electrode **270** is formed on substantially the entire surface of the substrate **110** as one planar electrode. In the exemplary embodiment, the resistance of the common electrode **270** may be reduced by connecting the common electrode **270** with the storage electrode line **131**. In this case, the same common voltage may be applied to the storage electrode line **131** and the common electrode **270**.

The common electrode **270** connects to the storage electrode line **131** at a place away from the microcavities **305** and specifically, away from the injection holes **307a**, **307b**, such that the connection does not interfere with injection of material into the microcavities **305**.

The common electrode **270** may be made of a transparent metal material such as indium tin oxide (ITO) and indium zinc oxide (IZO). A predetermined voltage may be applied to the common electrode **270**, and an electric field may be generated between the pixel electrode **191** and the common electrode **270**.

A first alignment layer **11** is formed on the pixel electrode **191**, and a second alignment layer **21** is formed below the common electrode **270** to face the first alignment layer **11**.

A liquid crystal layer containing liquid crystal molecules **310** is formed in the microcavity **305** positioned between the pixel electrode **191** and the common electrode **270**.

A third insulating layer **350** may be further formed on the common electrode **270**, and a roof layer **360** is formed on the third insulating layer **350**. The roof layer **360** may be made of an organic material. The microcavity **305** is formed below the roof layer **360**, and the roof layer **360** is hardened by a curing process to maintain the shape of the microcavity **305**. That is, the roof layer **360** is formed to be spaced apart from the pixel electrode **191** with the microcavity **305** therebetween.

The roof layer **360** is formed at each pixel PX along a pixel row and the second valley V2, and is formed in a partial region of the first valley V1. The roof layer **360** has substantially the same planar shape as the common electrode **270**. The common electrode **270** is formed in the partial region of the first valley V1 so as to be connected with the capacitive electrode **137**, and the roof layer **360** is formed at the corresponding portion. In the first valley V1 and the second valley V2, the microcavity **305** is not formed below the roof layer **360**, but formed to be attached to the substrate **110**. Accordingly, a thickness of the roof layer **360** positioned at the first valley V1 and the second valley V2 may be larger than a thickness of the roof layer **360** positioned at each of the first subpixel PXa and the second subpixel PXb. The upper surface and both sides of the microcavity **305** are formed to be covered by the roof layer **360**.

An injection hole **307** exposing a part of the microcavity **305** is formed in the roof layer **360**.

A fourth insulating layer **370** may be further formed on the roof layer **360**, and an encapsulation layer **390** may be formed on the fourth insulating layer **370**.

Although not illustrated, polarizers may be further formed on upper and lower sides of the display device.

While this invention has been described in connection with what is presently considered to be practical exemplary embodiments, it is to be understood that the invention is not limited to the disclosed embodiments, but, on the contrary, is intended to cover various modifications and equivalent arrangements included within the spirit and scope of the appended claims.

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<Description of symbols>

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|                           |                             |
|---------------------------|-----------------------------|
| 121: Gate line            | 131: Storage electrode line |
| 137: Capacitive electrode | 171: Data line              |
| 171h: First data line     | 171l: Second data line      |
| 191: Pixel electrode      | 270: Common electrode       |
| 305: Microcavity          | 360: Roof layer             |
| 390: Encapsulation layer  |                             |

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What is claimed is:

1. A display device, comprising:

a substrate;  
a gate line, a data line, and a storage electrode line formed on the substrate;  
a thin film transistor connected to the gate line and the data line;  
a pixel electrode connected with the thin film transistor;  
a common electrode formed on the pixel electrode;  
a plurality of microcavities between the common electrode and the pixel electrode;  
a roof layer formed on the common electrode;  
a liquid crystal layer in the microcavity; and  
an encapsulation layer formed on the roof layer to seal the microcavity,  
wherein the common electrode is connected with the storage electrode line at a position adjacent to the data line, spaced apart from the microcavities.

2. The display device of claim 1, wherein:

the microcavities are disposed in a matrix form, and the display device further include first valleys positioned between the microcavities which are adjacent to each other in a column direction, and second valleys positioned between the microcavities which are adjacent to each other in a row direction.

3. The display device of claim 2, wherein:

the common electrode is connected with the storage electrode line at the second valley.

4. The display device of claim 3, wherein:

the data line includes a first data line and a second data line, and  
the first data line and the second data line are positioned at both edges of the second valley, respectively.

5. The display device of claim 4, further comprising:

an insulating layer formed between the storage electrode line and the common electrode, and  
a contact hole extending through the insulating layer to at least a part of the storage electrode line positioned between the first data line and the second data line, wherein the common electrode is connected with the storage electrode line through the contact hole.

6. The display device of claim 5, wherein:

the contact hole is formed between the first data line and the second data line without reaching the first data line or the second data line.

7. The display device of claim 4, wherein:

the thin film transistor includes a first thin film transistor and a second thin film transistor,  
the pixel electrode includes a first subpixel electrode and a second subpixel electrode,  
the first thin film transistor is connected with the first data line and the first subpixel electrode, and  
the second thin film transistor is connected with the second data line and the second subpixel electrode.

8. The display device of claim 7, wherein:

a data voltage applied to the second data line is different from a data voltage applied to the first data line.

9. The display device of claim 2, wherein:  
the common electrode is connected with the storage electrode line in the first valley.
10. The display device of claim 9, wherein:  
the common electrode is attached to the substrate in the first valley and the second valley.
11. The display device of claim 10, wherein:  
a portion of the common electrode that is attached to the substrate has an L-shape.
12. The display device of claim 9, further comprising: 10  
a capacitive electrode protruding from the storage electrode line,  
wherein the common electrode is directly connected with the capacitive electrode.
13. The display device of claim 12, further comprising: 15  
an insulating layer formed between the storage electrode line and the common electrode, and  
a contact hole extending through the insulating layer to at least a part of the capacitive electrode,  
wherein the common electrode is connected with the 20  
capacitive electrode through the contact hole.

\* \* \* \* \*

|                |                                                                  |         |            |
|----------------|------------------------------------------------------------------|---------|------------|
| 专利名称(译)        | 显示设备                                                             |         |            |
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| [标]申请(专利权)人(译) | 三星显示有限公司                                                         |         |            |
| 申请(专利权)人(译)    | 三星DISPLAY CO. , LTD.                                             |         |            |
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| 发明人            | CHAE, KYUNG TAE<br>KIM, WON TAE<br>LEE, SUN HWA                  |         |            |
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| 优先权            | 1020140044981 2014-04-15 KR                                      |         |            |
| 其他公开文献         | US20150293414A1                                                  |         |            |
| 外部链接           | <a href="#">Espacenet</a> <a href="#">USPTO</a>                  |         |            |

#### 摘要(译)

提出了一种能够降低公共电极的电阻的显示装置。显示装置包括：基板；栅极线，数据线和形成在基板上的存储电极线；薄膜晶体管连接到栅极线和数据线；像素电极与薄膜晶体管连接；形成在像素电极上的公共电极；公共电极和像素电极之间的多个微腔；在公共电极上形成顶层；微腔中的液晶层；形成在顶层上以封闭微腔的封装层，其中公共电极在与数据线相邻的位置处与存储电极线连接。

